ABSTRACT

The present discloses relates to a semiconductor device and a method of manufacturing the semiconductor device. A semiconductor device includes a stacked structure including insulating layers and conductive layers stacked alternately with each other, a channel structure passing through at least a portion of the stacked structure, and a memory layer interposed between the conductive layers and the channel structure, wherein the memory layer includes a floating gate arranged between the conductive layers and the channel structure.

FIG. 5